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APPLICATION NO. FILING DATE		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/812,443	03/30/2004	Hirofumi Harada	S004-5253	S004-5253 3384	
7590 10/31/2005			EXAMINER		
ADAMS & WILKS			TOLEDO, FERNANDO L		
31st Floor 50 Broadway			ART UNIT	PAPER NUMBER	
New York, NY 10004			2823		
			DATE MAILED: 10/31/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Application No.	Applicant(s)	1112				
Office Action Summary		10/812,443	HARADA, HIROFUMI					
		Examiner	Art Unit					
		Fernando L. Toledo	2823					
The MAILING DATE of Period for Reply	this communication app	ears on the cover sheet with the c		SS				
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).								
Status								
 1) ⊠ Responsive to communication(s) filed on 23 September 2005. 2a) ☐ This action is FINAL. 2b) ☒ This action is non-final. 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213. 								
Disposition of Claims	•							
4) ☐ Claim(s) 1-7 is/are pending in the application. 4a) Of the above claim(s) 2-7 is/are withdrawn from consideration. 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or election requirement.								
Application Papers								
9) ☐ The specification is objected to by the Examiner. 10) ☑ The drawing(s) filed on 30 March 2004 is/are: a) ☐ accepted or b) ☑ objected to by the Examiner. Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a). Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d). 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.								
Priority under 35 U.S.C. § 119								
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) □ All b) □ Some * c) ☒ None of: 1. ☒ Certified copies of the priority documents have been received. 2. □ Certified copies of the priority documents have been received in Application No 3. □ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received.								
Attachment(s) 1) Notice of References Cited (PTO-8 2) Notice of Draftsperson's Patent Dra 3) Information Disclosure Statement(s Paper No(s)/Mail Date	wing Review (PTO-948)	4) Interview Summary (Paper No(s)/Mail Dat 5) Notice of Informal Pa 6) Other:	te	2)				

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DETAILED ACTION

Priority

1. Acknowledgment is made of applicant's claim for foreign priority based on an application filed in Japan on 3 April 2003. It is noted, however, that applicant has not filed a certified copy of the 2003-099926 application as required by 35 U.S.C. 119(b).

Election/Restrictions

- 2. Applicant's election without traverse of Species I in the reply filed on 23 September 2005 is acknowledged.
- 3. Claims 2 7 are withdrawn from further consideration pursuant to 37 CFR 1.142(b) as being drawn to nonelected inventions, there being no allowable generic or linking claim. Election was made without traverse in the reply filed on 23 September 2005.

Drawings

4. Figure 2 should be designated by a legend such as --Prior Art-- because only that which is old is illustrated. See MPEP § 608.02(g). Corrected drawings in compliance with 37 CFR 1.121(d) are required in reply to the Office action to avoid abandonment of the application. The replacement sheet(s) should be labeled "Replacement Sheet" in the page header (as per 37 CFR 1.84(c)) so as not to obstruct any portion of the drawing figures. If the changes are not accepted by the examiner, the applicant will be notified and informed of any required corrective action in the next Office action. The objection to the drawings will not be held in abeyance.

Claim Rejections - 35 USC § 102

5. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (a) the invention was known or used by others in this country, or patented or described in a printed publication in this or a foreign country, before the invention thereof by the applicant for a patent.
- 6. Claim 1 is rejected under 35 U.S.C. 102(a) as being anticipated by Ninomiya (U. S. Patent 6,639,275 B1).
- In re claim 1, Ninomiya, in the U. S. Patent 6,639,275 B2; figures 1A 8B discloses, 7. carrying out an anisotropic etching (Figure 3B) for a region in which a trench is intended to be formed on a main surface of a semiconductor substrate of a first conductivity type to form the trench 13; forming a gate oxide film 14 over the main surface of the semiconductor substrate of the first conductivity type and along wall surface of the trench; depositing a polycrystalline silicon wafer 15 so as to overlie the gate oxide film, etching the polycrystalline silicon layer so as to remove the polycrystalline silicon layer overlying the main surface of the semiconductor substrate and so as to remove the polycrystalline layer within the trench to a predetermined depth from the main surface of the semiconductor substrate to form a gate electrode within the trench; implanting an impurity of a second conductivity type 16 into the main surface of the semiconductor substrate of the first conductivity type and thermally diffusing the impurity of the second conductivity type to form a body region of the second conductivity type; implanting an impurity of the first conductivity type into the main surface of the semiconductor substrate to form a source region 17 of the first conductivity type; implanting an impurity of the second conductivity type 16a into the main surface of the semiconductor substrate to form a body contact region of the second conductivity type; depositing an intermediate insulating film 20

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over the main surface of the semiconductor substrate and the gate electrode; etching back the

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intermediate insulating film overlaying the main surface of the semiconductor substrate so as to

entirely expose the source region and the body contact region constituting the main surface of the

semiconductor substrate (Figure 6B); and forming a source metal electrode 18 over the main

surface of the semiconductor substrate.

Conclusion

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Fernando L. Toledo whose telephone number is 571-272-1867.

The examiner can normally be reached on Mon-Thu 7am to 5:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Matthew Smith can be reached on 571-272-1907. The fax phone number for the

organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

applications is available through Private PAIR only. For more information about the PAIR

system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Fernando L. Toledo

Patent Examiner

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28 October 2005